

2N6203

SILICON BIPOLAR NPN POWER TRANSISTOR 12 W, in the 100 – 400 MHz Range

The silicon bipolar n-p-n transistor is designed for communications transceiver equipment, auto-oscillator and frequency multiplier circuits, common emitter.

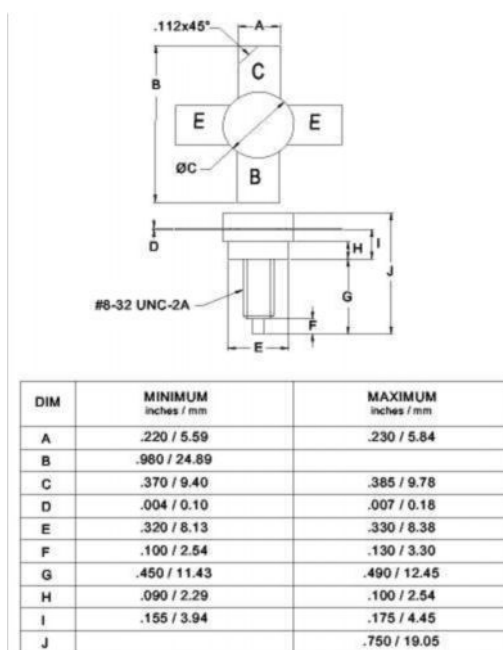
Features (At 400 MHz):

- Output Power: 12 W
- Power Gain: 6 dB Min
- Efficiency: 50% Min

Absolute Maximum Ratings

Parameters	Sym	Value	Unit
Collector–Emitter Voltage	V_{CEO}	33	V_{DC}
Collector–Emitter Voltage	V_{CER}	60	V_{DC}
Collector-Base Voltage	V_{CBO}	60	V_{DC}
Emitter–Base Voltage	V_{EBO}	4	V_{DC}
Collector Current	I_C	1	A_{DC}
Operation Junction Temperature	T_j	-65 ÷ +200	°C
Storage Temperature Range	T_{STG}	-65 ÷ +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	8.8	°C/W
Total Power Dissipation, $T_C=25^\circ\text{C}$	P_D	15	W

PACKAGE STYLE .380 4L STUD



Parameters

Parameter	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage ($I_C = 200 \text{ mA}$, $I_B = 0 \text{ A}$)	$V_{(BR)CEO}$	33	—	—	V_{DC}
Collector–Emitter Breakdown Voltage ($I_C = 1 \text{ A}$, $V_{BE} = 0 \text{ V}$)	$V_{(BR)CER}$	60	—	—	V_{DC}
Emitter–Base Breakdown Voltage ($I_E = 2.5 \text{ mA}$, $I_C = 0 \text{ A}$)	$V_{(BR)EBO}$	4	—	—	V_{DC}
DC Current Gain ($V_{CE} = 5 \text{ V}$, $I_C = 0.25 \text{ A}$)	h_{FE}	5	—	100	
Power Gain ($V_{CC} = 28 \text{ V}$, $P_{OUT} = 12 \text{ W}$, $f = 400 \text{ MHz}$)	G_p	6	—	—	dB
Drain Efficiency ($V_{CC} = 28 \text{ V}$, $P_{OUT} = 12 \text{ W}$, $f = 400 \text{ MHz}$)	η_C	50	70	—	%

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Specification is subject to change without notice